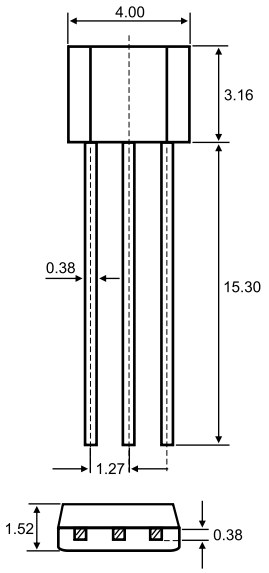
2SD2470

TO-92S Transistor (NPN)

1 2 3

1. EMITTER
2. COLLECTOR
3. BASE

TO-92S



Dimensions in inches and (millimeters)

Features

✧ Low saturation voltage $V_{CE(sat)}$:0.5V

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	15	V
V_{CEO}	Collector-Emitter Voltage	10	V
V_{EBO}	Emitter-Base Voltage	8	V
I_C	Collector Current –Continuous	5	A
P_C	Collector Power Dissipation	400	mW
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (T_A=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=50μA , I_E=0	15			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA, I_B=0	10			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=50μA, I_C=0	8			V
Collector cut-off current	I_{CBO}	V_{CB}=10V, I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=8V, I_C=0			0.5	μA
DC current gain	h_{FE}	V_{CE}=2V, I_C=2A	270		820	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=3A,I_B=0.1A			0.5	V
Transition frequency	f_T	V_{CE}=6V, I_C=50mA,f=100MHz		170		MHz
Collector output capacitance	C_{ob}	V_{CB}=10V,I_E=0,f=1MHz		30		pF

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Typical Characteristics